



## GLT44016

### 256K X 16 CMOS DYNAMIC RAM WITH EXTENDED DATA OUTPUT

Nov, 2004(Rev.3.5)

#### Features :

- \* 262,144 words by 16 bits organization.
- \* Fast access time and cycle time.
- \* Dual  $\overline{\text{CAS}}$  Input.
- \* Low power dissipation.
- \* Read-Modify-Write,  $\overline{\text{RAS}}$ -Only Refresh,  $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$  Refresh, Hidden Refresh and Test Mode Capability.
- \* 512 refresh cycles per 8ms.
- \* Available in 40-Pin 400 mil SOJ and 40/44 Pin TSOP(II)
- \* Single 5.0V $\pm$ 5% Power Supply.
- \* All inputs and Outputs are TTL compatible.
- \* Extended Data-Out(EDO) Page Mode operation.

#### Description :

The GLT44016 is a 262,144 x 16 bit high-performance CMOS dynamic random access memory. The GLT44016 offers Fast Page mode with Extended Data Output, and has both BYTE WRITE and WORD WRITE access cycles via two  $\overline{\text{CAS}}$  pins. The GLT44016 has symmetric address and accepts 512-cycle refresh in 8ms interval.

All inputs are TTL compatible. EDO Page Mode operation allows random access up to 512 x 16 bits within a page, with cycle times as short as 10ns.

The GLT44016 is best suited for graphics, and DSP applications requiring high performance memories.

HIGH PERFORMANCE	25	28	30	35	40	50
Max. $\overline{\text{RAS}}$ Access Time, ( $t_{\text{RAC}}$ )	25 ns	28 ns	30 ns	35 ns	40 ns	50 ns
Max. Column Address Access Time, ( $t_{\text{CAA}}$ )	13 ns	13 ns	16 ns	18 ns	20 ns	25 ns
Min. Extended Data Out Page Mode Cycle Time, ( $t_{\text{PC}}$ )	10 ns	10 ns	12 ns	13 ns	15 ns	20 ns
Min. Read/Write Cycle Time, ( $t_{\text{RC}}$ )	45 ns	45 ns	60 ns	65 ns	70 ns	85 ns
Max. $\overline{\text{CAS}}$ Access Time ( $t_{\text{CAC}}$ )	8 ns	8 ns	10 ns	11 ns	12 ns	14 ns

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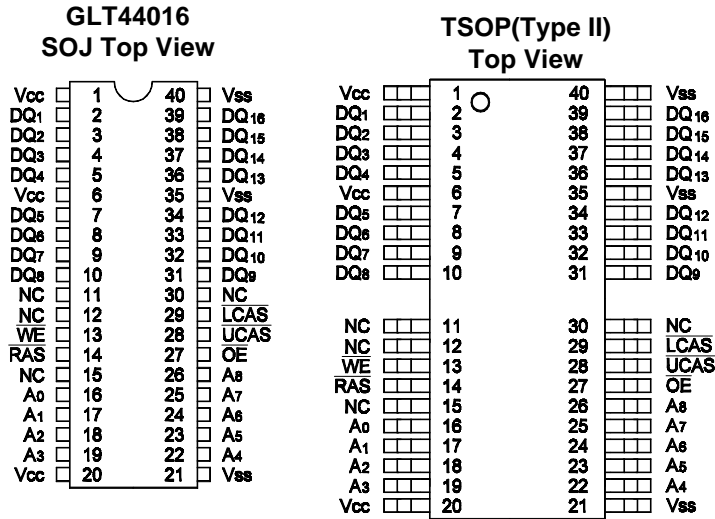


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**Pin Configuration :**



**Pin Descriptions:**

Name	Function
A <sub>0</sub> - A <sub>8</sub>	Address Inputs
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{UCAS}}$	Column Address Strobe/Upper Byte Control
$\overline{\text{LCAS}}$	Column Address Strobe/Lower Byte Control
$\overline{\text{WE}}$	Write Enable
$\overline{\text{OE}}$	Output Enable
DQ <sub>1</sub> - DQ <sub>16</sub>	Data Inputs / Outputs
V <sub>CC</sub>	+5V Power Supply
V <sub>SS</sub>	Ground
NC	No Connection

**Absolute Maximum Ratings\***

Operating Temperature,  $T_A$  (ambient)  
 .....-0°C to +70°C  
 Storage Temperature(plastic).....-55°C to +150°C  
 Voltage Relative to  $V_{SS}$ .....-1.0V to + 7.0V  
 Short Circuit Output Current.....50mA  
 Power Dissipation.....1.0W

\*Note: Operation above Absolute Maximum Ratings can adversely affect device reliability.

**Capacitance\***

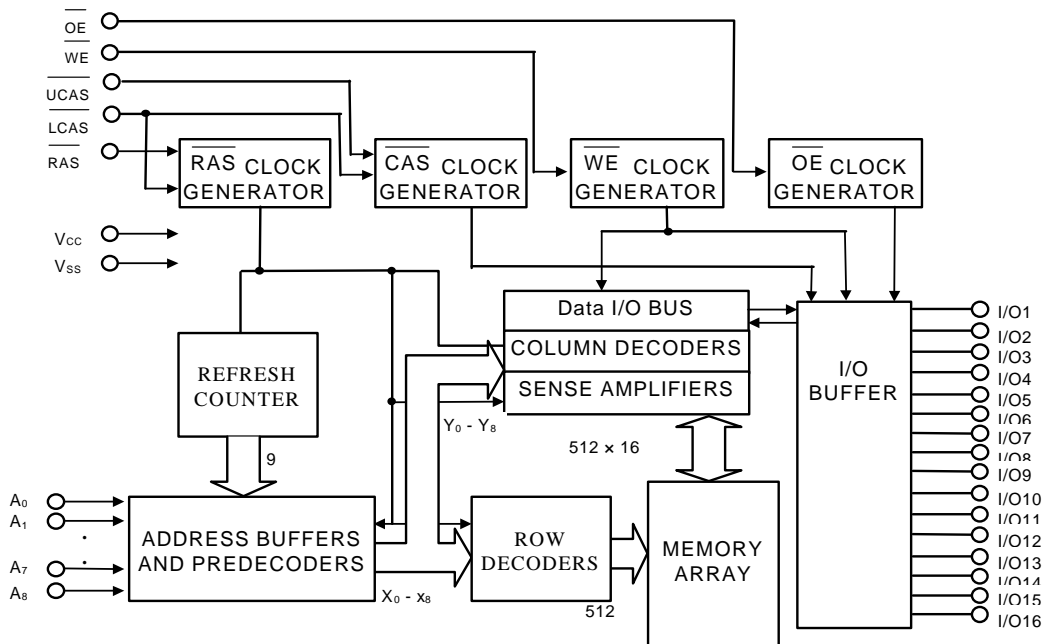
$T_A=25^\circ\text{C}$ ,  $V_{CC}=5V\pm 5\%$ ,  $V_{SS}=0V$

Symbol	Parameter	Max.	Unit
$C_{IN1}$	Address Input	5	pF
$C_{IN2}$	$\overline{\text{RAS}}$ , $\overline{\text{LCAS}}$ , $\overline{\text{UCAS}}$ , $\overline{\text{WE}}$ , $\overline{\text{OE}}$	7	pF
$C_{OUT}$	Data Input/Output	7	pF

\*Note: Capacitance is sampled and not 100% tested

**Electrical Specifications**

- CAS means  $\overline{\text{UCAS}}$  and  $\overline{\text{LCAS}}$ .
- All voltages are referenced to GND.
- After power up, wait more than 100 $\mu\text{s}$  and then, execute eight  $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$  or  $\overline{\text{RAS}}$ -only refresh cycles as dummy cycles to initialize internal circuit.

**Block Diagram :**


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**Truth Table: GLT44016**

Function		RAS	CASL	CASH	WE	OE	ADDRESS	DQs	Notes
Standby		H	H→X	H→X	X	X		High-Z	
Read: Word		L	L	L	H	L	ROW/COL	Data Out	
Read: Lower Byte		L	L	H	H	L	ROW/COL	Lower Byte,Data-Out Upper Byte,High-Z	
Read: Upper Byte		L	H	L	H	L	ROW/COL	Lower Byte,High-Z Upper Byte,Data-Out	
Write: Word(Early Write)		L	L	L	L	X	ROW/COL	Data-In	
Write: Lower Byte (Early)		L	L	H	L	X	ROW/COL	Lower Byte,Data-In Upper Byte,High-Z	
Write: Upper Byte (Early)		L	H	L	L	X	ROW/COL	Lower Byte,High-Z Upper Byte,Data-In	
Read Write		L	L	L	H→L	L→H	ROW/COL	Data-Out,Data-In	1,2
EDO-Page- Mode Read	1st Cycle	L	H→L	H→L	H	L	ROW/COL	Data-Out	1
	2nd Cycle	L	H→L	H→L	H	L	COL	Data-Out	1
EDO-Page- Mode Write	1st Cycle	L	H→L	H→L	L	X	ROW/COL	Data-In	2
	2nd Cycle	L	H→L	H→L	L	X	COL	Data-In	2
EDO-Page- Mode Read- Write	1st Cycle	L	H→L	H→L	H→L	L→H	ROW/COL	Data-Out,Data-In	1,2
	2nd Cycle	L	H→L	H→L	H→L	L→H	COL	Data-Out,Data-In	1,2
Hidden Refresh	Read	L→H→L	L	L	H	L	ROW/COL	Data-Out	1
	Write	L→H→L	L	L	L	X	ROW/COL	Data-In	2,3
RAS-Only Refresh		L	H	H	X	X	ROW	High-Z	
CBR Refresh		H→L	L	L	X	X		High-Z	4

**Notes:**

1. These READ cycles may also be BYTE READ cycles (either  $\overline{UCAS}$  or  $\overline{LCAS}$  active).
2. These WRITE cycles may also be BYTE WRITE cycles (either  $\overline{UCAS}$  or  $\overline{LCAS}$  active).
3. EARLY WRITE only.
4. At least one of the two CAS signals must be active ( $\overline{UCAS}$  or  $\overline{LCAS}$ ).

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**DC and Operating Characteristics (1-2)**
 $T_A = 0^\circ\text{C to } 70^\circ\text{C}$ ,  $V_{CC}=5V\pm 5\%$ ,  $V_{SS}=0V$ , unless otherwise specified.

Sym.	Parameter	Test Conditions	Access Time	Min.	Typ	Max.	Unit	Notes
$I_{LI}$	Input Leakage Current (any input pin)	$0V \leq V_{IN} \leq 5.5V$ (All other pins not under test=0V)		-10		+10	$\mu\text{A}$	
$I_{LO}$	Output Leakage Current (for High-Z State)	$0V \leq V_{out} \leq 5.5V$ Output is disabled (HiZ)		-10		+10	$\mu\text{A}$	
$I_{CC1}$	Operating Current, Random READ/WRITE	$t_{RC} = t_{RC}(\text{min.})$	$t_{RAC} = 25\text{ns}$ $t_{RAC} = 28\text{ns}$ $t_{RAC} = 30\text{ns}$ $t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			270 270 250 210 190 170	mA	1,2
$I_{CC2}$	Standby Current,(TTL)	$\overline{\text{RAS}}, \overline{\text{UCAS}}, \overline{\text{LCAS}}$ at $V_{IH}$ other inputs $\geq V_{SS}$				4	mA	
$I_{CC3}$	Refresh Current, $\overline{\text{RAS}}$ -Only	$\overline{\text{RAS}}$ cycling, $\overline{\text{UCAS}},$ $\overline{\text{LCAS}}$ at $V_{IH}$ $t_{RC} = t_{RC}(\text{min.})$	$t_{RAC} = 25\text{ns}$ $t_{RAC} = 28\text{ns}$ $t_{RAC} = 30\text{ns}$ $t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			270 270 250 210 190 170	mA	2
$I_{CC4}$	Operating Current, EDO Page Mode	$\overline{\text{RAS}}$ at $V_{IL}$ , $\overline{\text{UCAS}}, \overline{\text{LCAS}}$ address cycling: $t_{PC}=t_{PC}(\text{min.})$	$t_{RAC} = 25\text{ns}$ $t_{RAC} = 28\text{ns}$ $t_{RAC} = 30\text{ns}$ $t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			270 270 250 210 190 170	mA	1,2
$I_{CC5}$	Refresh Current, CAS Before RAS	$\overline{\text{RAS}}, \overline{\text{UCAS}}, \overline{\text{LCAS}}$ address cycling: $t_{RC}=t_{RC}(\text{min.})$	$t_{RAC} = 25\text{ns}$ $t_{RAC} = 28\text{ns}$ $t_{RAC} = 30\text{ns}$ $t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			270 270 250 210 190 170	mA	1
$I_{CC6}$	Standby Current, (CMOS)	$\overline{\text{RAS}} \geq V_{CC}-0.2V,$ $\overline{\text{UCAS}} \geq V_{CC}-0.2V,$ $\overline{\text{LCAS}} \geq V_{CC}-0.2V,$ All other inputs $V_{SS}$				2	mA	
$V_{IL}$	Input Low Voltage			-1		+0.8	V	3
$V_{IH}$	Input High Voltage			2.4		$V_{CC}+1$	V	3
$V_{OL}$	Output Low Voltage	$I_{OL} = 4.2\text{mA}$				0.4	V	
$V_{OH}$	Output High Voltage	$I_{OH} = -5.0\text{mA}$		2.4			V	

**Notes:**

- $I_{CC}$  is dependent on output loading when the device output is selected. Specified  $I_{CC}(\text{max.})$  is measured with the output open.
- $I_{CC}$  is dependent upon the number of address transitions specified  $I_{CC}(\text{max.})$  is measured with a maximum of one transition per address cycle in random Read/Write and EDO Fast Page Mode.
- Specified  $V_{IL}(\text{min.})$  is steady state operation. During transitions  $V_{IL}(\text{min.})$  may undershoot to -1.0V for a period not to exceed 20ns. All AC parameters are measured with  $V_{IL}(\text{min.}) \geq V_{SS}$  and  $V_{IH}(\text{max.}) \leq V_{CC}$ .



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**AC Characteristics**

T<sub>A</sub> = 0°C to 70°C , V<sub>CC</sub> = 5 V ± 5%, V<sub>IH</sub>/V<sub>IL</sub> = 2.4/0.8 V, V<sub>OH</sub>/V<sub>OL</sub> = 2.0/0.8V

An initial pause of 100 μs and 8 CAS -before- RAS or RAS-only refresh cycles are required after power-up.

Parameter	Symbol	25		28		30		35		40		50		Unit	Notes
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Read or Write Cycle Time	t <sub>RC</sub>	45		45		60		65		70		85		ns	
Read Modify Write Cycle Time	t <sub>RWC</sub>	67		67		79		86		91		106		ns	
RAS Precharge Time	t <sub>RP</sub>	15		15		25		25		25		30		ns	
RAS Pulse Width	t <sub>RAS</sub>	25	100k	28	100k	30	100k	35	100k	40	100k	50	100k	ns	
Access Time from RAS	t <sub>RAC</sub>		25		28		30		35		40		50	ns	1,2,3
Access Time from CAS	t <sub>CAC</sub>		8		8		10		11		12		14	ns	1,5,10
Access Time from Column Address	t <sub>AA</sub>		13		13		16		18		20		25	ns	1,5,6
CAS to Output Low-Z	t <sub>CLZ</sub>		0		0	0		0		0		0		ns	
CAS to Output High-Z	t <sub>CEZ</sub>	0	5	0	5	3	7	3	8	3	8	3	8	ns	
RAS Hold Time	t <sub>RSH</sub>	7		7		7		8		8		8		ns	
RAS Hold Time Referenced to OE	t <sub>ROH</sub>	4		4		7		8		8		8		ns	
CAS Hold Time	t <sub>CSH</sub>	25		25		25		30		35		42		ns	
CAS Pulse Width	t <sub>CAS</sub>	4		4		4.5		5		6		8		ns	
RAS to CAS Delay Time	t <sub>RCD</sub>	10	17	10	17	10	20	11	24	12	28	13	36	ns	
RAS to Column Address Delay Time	t <sub>RAD</sub>	8	12	8	12	8	14	9	17	10	20	11	25	ns	7
CAS to RAS Precharge Time	t <sub>CRP</sub>	5		5		5		5		5		5		ns	
Row Address Set-Up Time	t <sub>ASR</sub>	0		0		0		0		0		0		ns	
Row Address Hold Time	t <sub>RAH</sub>	4		4		6		7		8		9		ns	
Column Address Set-Up Time	t <sub>ASC</sub>	0		0		0		0		0		0		ns	
Column Address Hold Time	t <sub>CAH</sub>	4		4		5		6		6		7		ns	
Column Address to RAS Lead Time	t <sub>RAL</sub>	13		13		16		18		20		25		ns	
Column Address Hold Time Referenced to RAS	t <sub>AR</sub>	19		19		25		30		34		35		ns	
Read Command Set-Up Time	t <sub>RCS</sub>	0		0		0		0		0		0		ns	
Read Command Hold Time Referenced to CAS	t <sub>RCH</sub>	0		0		0		0		0		0		ns	4
Read Command Hold Time Referenced to RAS	t <sub>RRH</sub>	0		0		0		0		0		0		ns	4
Write Command Set-Up Time	t <sub>WCS</sub>	0		0		0		0		0		0		ns	8,9
Write Command Hold Time	t <sub>WCH</sub>	4		4		5		6		6		6		ns	
Write Command Pulse Width	t <sub>WP</sub>	4		4		5		6		6		6		ns	
Write Command to RAS Lead Time	t <sub>RWL</sub>	7		7		7		8		8		8		ns	
Write Command to CAS Lead Time	t <sub>CWL</sub>	5		5		6		7		7		7		ns	

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**AC Characteristics**

Parameter	Symbol	25		28		30		35		40		50		Unit	Notes
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Data Set-Up Time	$t_{DS}$	0	0	0	0	0		0		0		0		ns	
Data Hold Time	$t_{DH}$	4		4		7		8		8		8		ns	
Data Hold Time Referenced to RAS	$t_{DHR}$	19		19		27		32		36		37		ns	
RAS to WE E Delay Time	$t_{RWD}$	36		36		43		49		54		64		ns	
CAS to WE Delay Time	$t_{CWD}$	19		19		21		23		24		26		ns	
Column Address to WE Delay Time	$t_{AWD}$	24		24		27		30		32		37		ns	
RAS to CAS Precharge Time	$t_{RPC}$	0		0		0		0		0		0		ns	
Access Time from CAS Precharge	$t_{CPA}$	15		15			18		20		22		27	ns	
EDO Page Mode Cycle Time	$t_{PC}$	10		10		12		13		15		20		ns	
EDO Page Mode Read-Modify-Write Cycle Time	$t_{PRWC}$	35		35		39		43		45		50		ns	
CAS Precharge Time (EDO Page Mode)	$t_{CP}$	4		4		4.5		5		6		8		ns	
RAS Pulse Width (EDO Page Mode Only)	$t_{RASP}$	25	100k	28	100k	30	100k	35	100k	40	100k	50	100k	ns	
Access Time from OE	$t_{OEA}$		8		8		10		11		12		14	ns	
OE to Data Delay Time	$t_{OED}$	5		5		7		8		8		8		ns	
OE to Output High-Z	$t_{OEZ}$	3	7	3	7	3	7	3	8	3	8	0	8	ns	
OE Command Hold Time	$t_{OEH}$	5		5		6		6		7		7		ns	
Data Output Hold after CAS low	$t_{DOH}$	4		4		5		5		5		5		ns	
RAS to Output High-Z	$t_{REZ}$	3	7	3	7	3	7	3	8	3	8	3	8	ns	
WE to Output High-Z	$t_{WEZ}$	3	10	3	10	3	10	3	10	3	10	3	12	ns	
OE to CAS Hold Time	$t_{OCH}$	8		8		8		8		8		8		ns	
CAS Hold Time to OE	$t_{CHO}$	8		8		8		8		8		8		ns	
OE Precharge Time	$t_{OEP}$	8		8		8		8		8		8		ns	
CAS Set-Up Time for CAS-before-RAS Cycle	$t_{CSR}$	5		5		10		10		10		10		ns	
CAS Hold Time for CAS-before-RAS Cycle	$t_{CHR}$	6		6		7		8		8		10		ns	
Transition Time	$t_T$	1.5	50	1.5	50	1.5	50	1.5	50	1.5	50	2	50	ns	
Refresh Period	$t_{REF}$		8		8		8		8		8		8	ms	

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**Notes:**

1. Measure with a load equivalent to one TTL inputs and 50 pF.
2. Assumes that  $t_{RCD} \leq t_{RCD}(\text{max.})$ . If  $t_{RCD}$  is greater than  $t_{RCD}(\text{max.})$ , access time will be  $t_{AA}$  dominant.
3. Assumes that  $t_{RAD} \leq t_{RAD}(\text{max.})$ . If  $t_{RAD}$  is greater than  $t_{RCD}(\text{max.})$ , access time will be controlled by  $t_{CAC}$ .
4. Either  $t_{RRH}$  or  $t_{RCH}$  must be satisfied for a Read Cycle.
5. Access time is determined by the longest of  $t_{CAA}$ ,  $t_{CAC}$  and  $t_{CPA}$ .
6. Assumes that  $t_{RAD} \geq t_{RAD}(\text{max.})$ .
7. Operation within the  $t_{RAD}(\text{max.})$  limit ensures that  $t_{RAC}(\text{max.})$  can be met.  $t_{RAD}(\text{max.})$  is specified as a reference point only. If  $t_{RAD}$  is greater than the specified  $t_{RAD}(\text{max.})$  limit, the access time is controlled by  $t_{CAA}$  and  $t_{CAC}$ .
8.  $t_{WCS}$ ,  $t_{RWD}$ ,  $t_{AWD}$  and  $t_{CWD}$  are not restrictive operating parameters.
9.  $t_{WCS}(\text{min.})$  must be satisfied in an Early Write Cycle.
10.  $t_{DS}$  and  $t_{DH}$  are referenced to the latter occurrence of  $\overline{\text{CAS}}$  of  $\overline{\text{WE}}$ .  
 $t_T$  is measured between  $V_{IH}(\text{min.})$  and  $V_{IL}(\text{max.})$ . AC-measurements assume  $t_T = 1.5 \text{ ns}$ .

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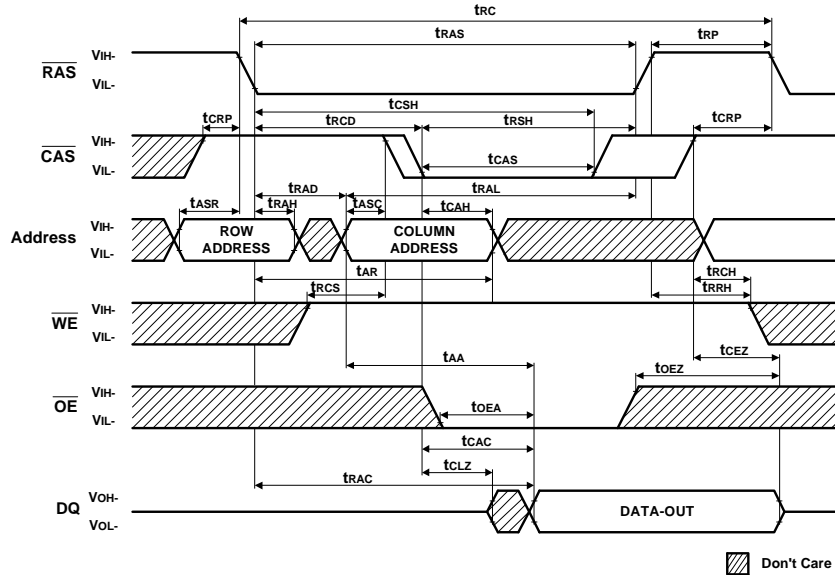
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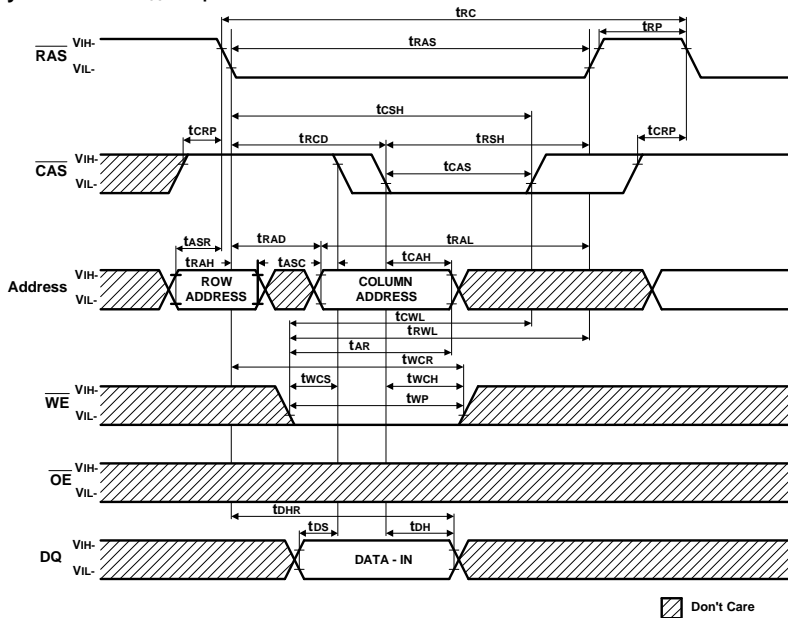
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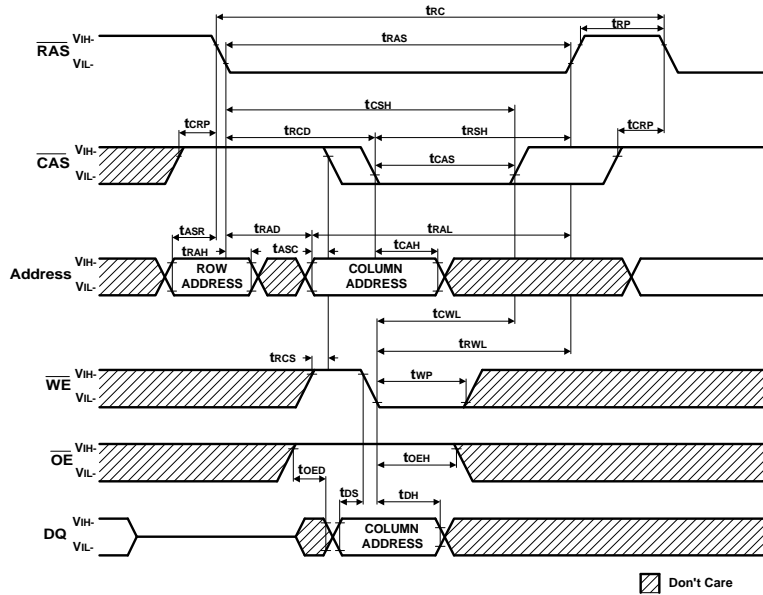
**Read Cycle**



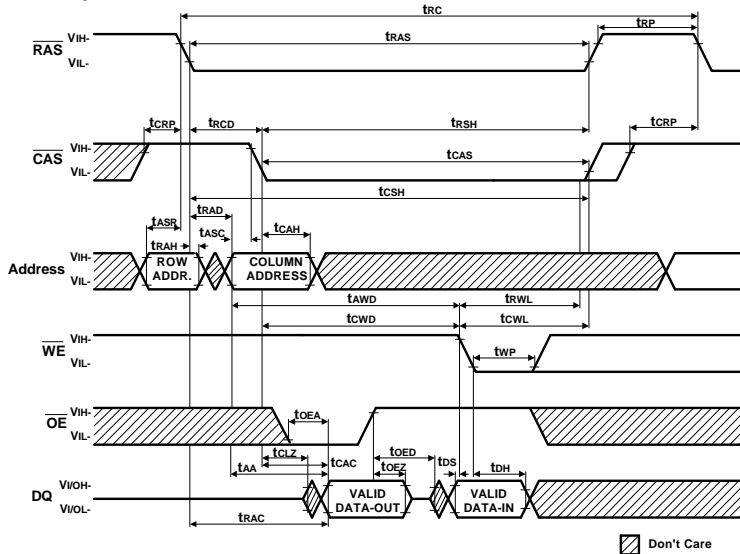
**Early Write Cycle NOTE : D<sub>OUT</sub> = Open**



**Late Write Cycle (OE Controlled Write) NOTE : D<sub>OUT</sub> = Open**

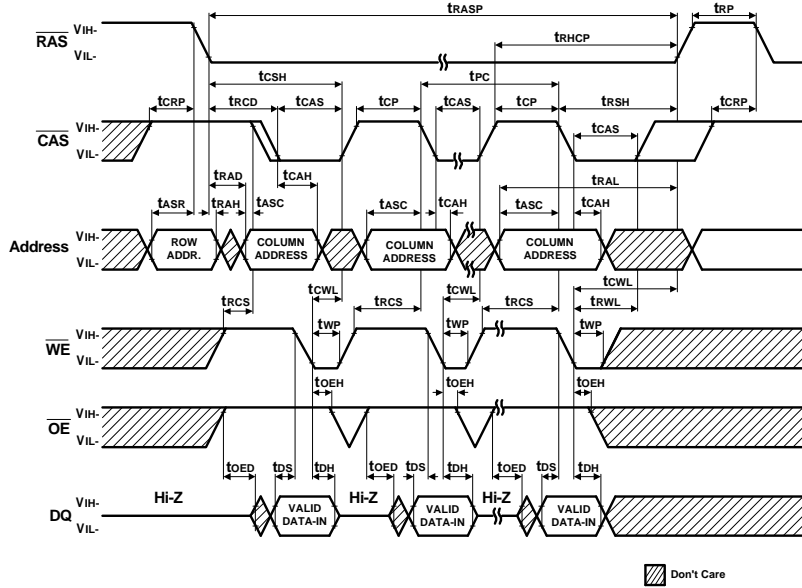


**Read - Modify - Write Cycle**

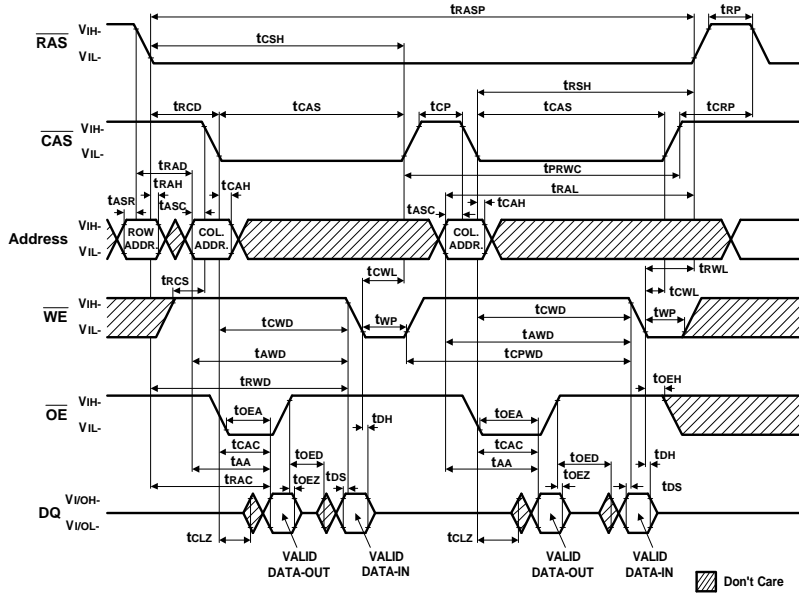




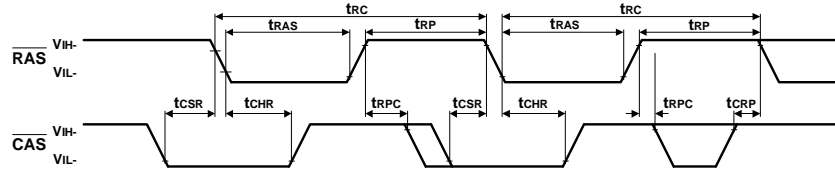
**EDO Page Mode Late Write Cycle**



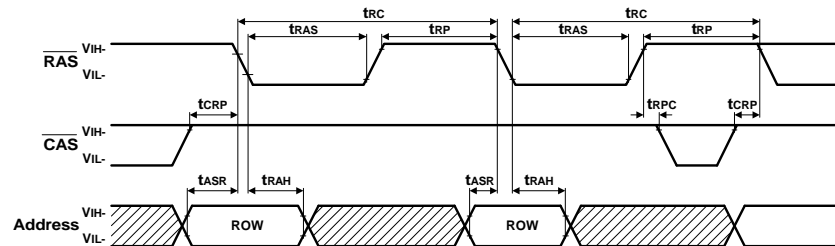
**EDO Page Read - Modify - Write Cycle**



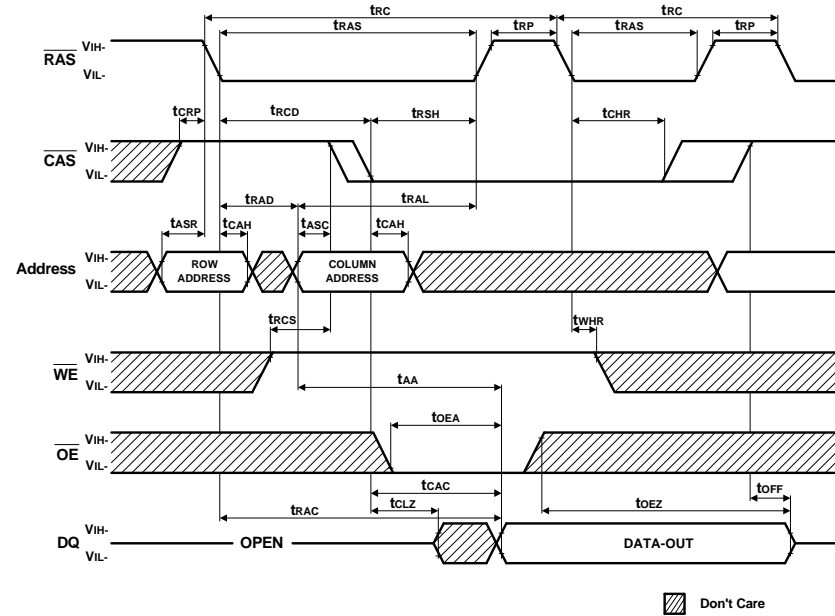
**CAS Before RAS Refresh Cycle**



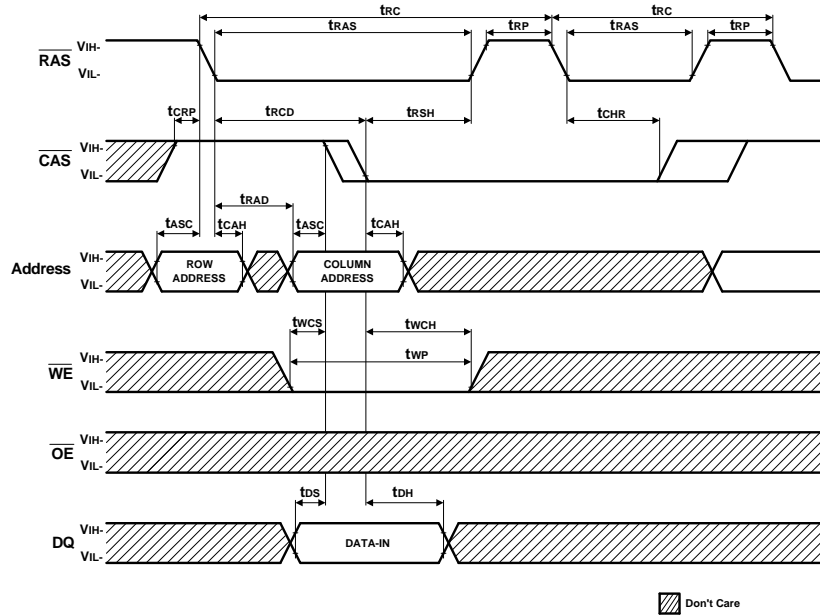
**RAS -Only Refresh Cycle**



**Hidden Refresh Cycle ( Read )**



**Hidden Refresh Cycle ( Write ) NOTE : D<sub>OUT</sub> =Open**







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**Ordering Information**

<b>Part Number</b>	<b>SPEED</b>	<b>POWER</b>	<b>FEATURE</b>	<b>PACKAGE</b>
GLT44016-25J4	25ns	Normal	EDO	40L 400mil SOJ
GLT44016-28J4	28ns	Normal	EDO	40L 400mil SOJ
GLT44016-30J4	30ns	Normal	EDO	40L 400mil SOJ
GLT44016-35J4	35ns	Normal	EDO	40L 400mil SOJ
GLT44016-40J4	40ns	Normal	EDO	40L 400mil SOJ
GLT44016-50J4	50ns	Normal	EDO	40L 400mil SOJ
GLT44016P-25J4	25ns	Normal	EDO	40L 400mil SOJ
GLT44016P-28J4	28ns	Normal	EDO	40L 400mil SOJ
GLT44016P-30J4	30ns	Normal	EDO	40L 400mil SOJ
GLT44016P-35J4	35ns	Normal	EDO	40L 400mil SOJ
GLT44016P-40J4	40ns	Normal	EDO	40L 400mil SOJ
GLT44016P-50J4	50ns	Normal	EDO	40L 400mil SOJ
GLT44016-25TC	25ns	Normal	EDO	44L 400mil TSOP
GLT44016-28TC	28ns	Normal	EDO	44L 400mil TSOP
GLT44016-30TC	30ns	Normal	EDO	44L 400mil TSOP
GLT44016-35TC	35ns	Normal	EDO	44L 400mil TSOP
GLT44016-40TC	40ns	Normal	EDO	44L 400mil TSOP
GLT44016-50TC	50ns	Normal	EDO	44L 400mil TSOP
GLT44016P-25TC	25ns	Normal	EDO	44L 400mil TSOP
GLT44016P-28TC	28ns	Normal	EDO	44L 400mil TSOP
GLT44016P-30TC	30ns	Normal	EDO	44L 400mil TSOP
GLT44016P-35TC	35ns	Normal	EDO	44L 400mil TSOP
GLT44016P-40TC	40ns	Normal	EDO	44L 400mil TSOP
GLT44016P-50TC	50ns	Normal	EDO	44L 400mil TSOP

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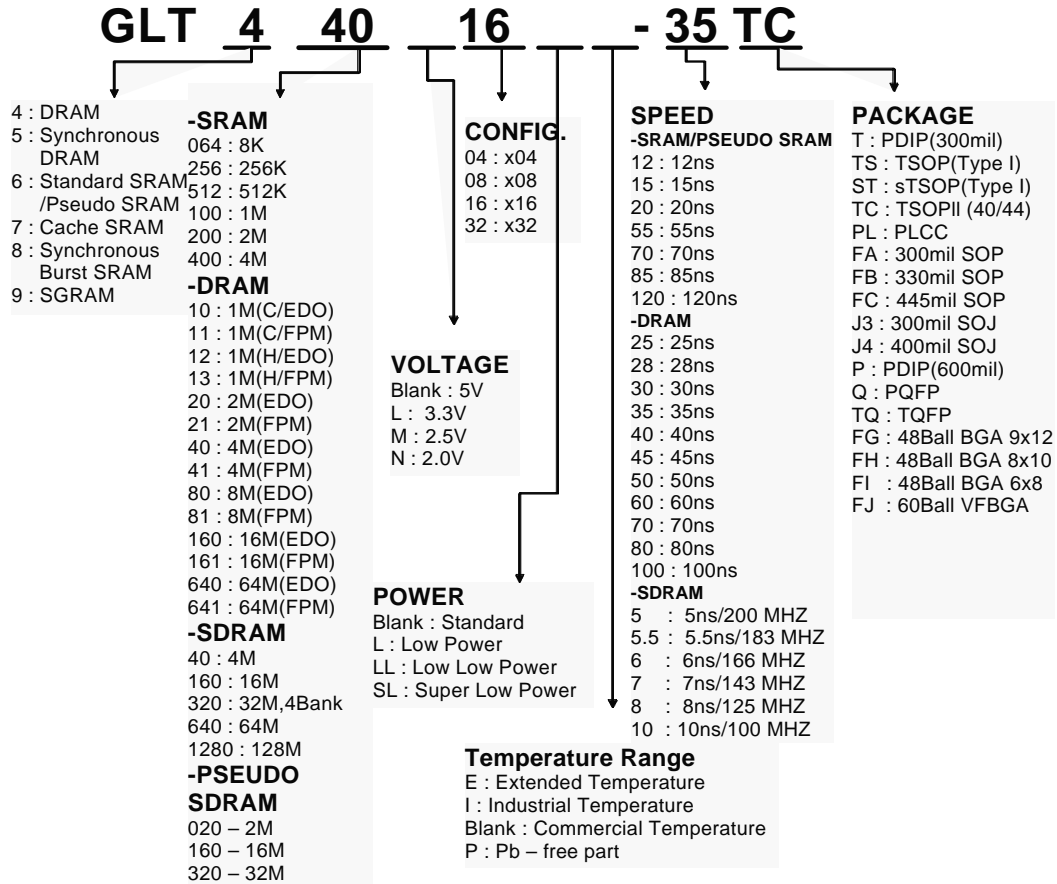
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TEL : 886-2-27968078

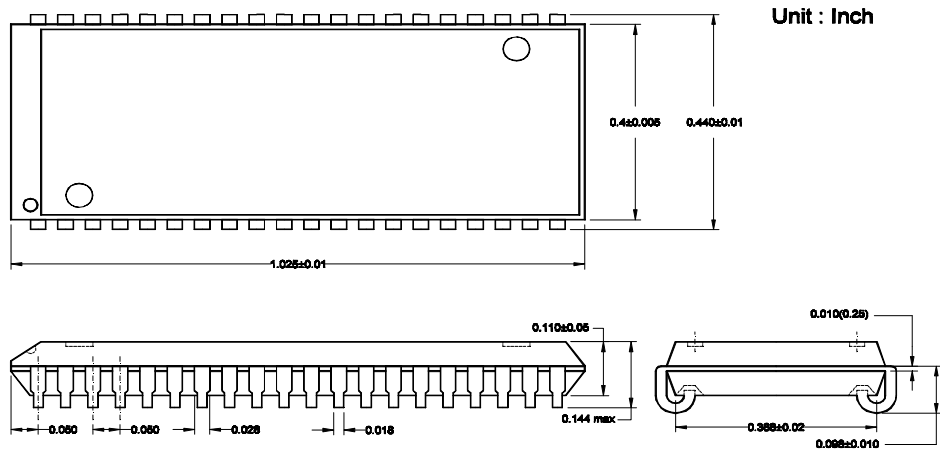
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**Parts Numbers (Top Mark) Definition for DRAM :**


**Package Information**

400 mil 40 Pin Small Outline J-form Package (SOJ)



40/44 Lead Thin Small Outline Package TSOP(Type II)

